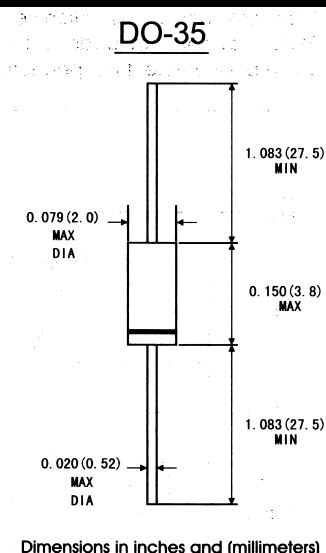


FEATURES

- The zener voltage are graded according to the international E24 standard .Other voltage tolerance and higher zener voltage on request.

MECHANICAL DATA

- Case:** DO-35 glass case
- Polarity:** Color band denotes cathode end
- Weight:** Approx. 0.13gram



ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES)(TA=25°C)

	Symbols	Value	Units
Zener current see table "Characteristics"			
Power dissipation at TA=50°C	P _{tot}	500 ¹⁾	mW
Junction temperature	T _J	175	°C
Storage temperature range	T _{STG}	-65 to + 175	°C

1)Valid provided that at a distance of 8mm from case are kept at ambient temperature

ELECTRICAL CHARACTERISTICS(TA=25°C)

	Symbols	Min.	Typ.	Max.	Units
Thermal resistance junction to ambient	R θ JA			300 ¹⁾	K/W
Forward voltage at IF=100mA	V _F			1	V

1)Valid provided that leads at a distance of 8mm from case are kept at ambient temperature

BZX55... SILICON PLANAR ZENER DIODES

Type	Zener Voltage Range1)			Dynamic resistance			Reverse leakage current			Temp coefficient of zener voltage
	VZNOM	IZT for VZT 2)		r _{zjt} and r _{zjk} at I _{zk}			I _R and I _{R 2)} at V _R			TK _{vz}
	V	mA	V	Ω	Ω	mA	μ A	μ A	V	%/K
BZX 55/C 0V8 3)	0.8	5	0.73.0.83	<8	<50	1	-	-	-	-0.26...-0.23
BZX 55/C 2V0	2.0		1.9.2.1	<85	<600		<100	<200	<1	-0.09...-0.06
BZX 55/C 2V4	2.4		2.28.2.56				<50	<100		
BZX 55/C 2V7	2.7		2.5.2.9				<10	<50		
BZX 55/C 3V0	3		2.8.3.2				<4	<40		-0.08...-0.05
BZX 55/C 3V3	3.3		3.1.3.5							
BZX 55/C 3V6	3.6		3.4.3.8							
BZX 55/C 3V9	3.9		3.7.4.1				<75	<1		<20
BZX 55/C 4V3	4.3		4.4.5.0	<60				<0.5		<10
BZX 55/C 4V7	4.7		4.8.5.4	<35			<550	<0.1		<2
BZX 55/C 5V1	5.1		5.2.6.0	<25	<450		3.0		0.03.0.07	
BZX 55/C 5V6	5.6		5.8.6.6	<10	<200		5.0		0.03.0.07	
BZX 55/C 6V2	6.2		6.4.7.2	<8	<150		6.2		0.03.0.08	
BZX 55/C 6V8	6.8		7.0.7.9	<7	<50		6.8		0.03.0.09	
BZX 55/C 7V5	7.5		7.7.8.7	<7			7.5		0.03.0.1	
BZX 55/C 8V2	8.2		8.5.9.6	<10			8.2		0.03.0.11	
BZX 55/C 9V1	9.1		9.4.10.6	<15	<70		9.1			
BZX 55/C 10	10		10.4.11.6	<20	<70		10.0			
BZX 55/C 11	11		11.4.12.7	<20	<90		11.0			
BZX 55/C 12	12		12.4.14.1	<26	<110		12			
BZX 55/C 13	13		13.8.15.6	<30	<110		13			
BZX 55/C 15	15		15.3.17.1	<40	<170		15			
BZX 55/C 16	16		16.8.19.1	<50	<170					
BZX 55/C 18	18		18.8.21.2	<55	<220					
BZX 55/C 20	20									

BZX55... SILICON PLANAR ZENER DIODES

BZX 55/C 22	22	5	20.8.23.3	<55	<220	1	<0.1	<2	16	0.04.0.12		
BZX 55/C 24	24		22.8.25.6	<80					18			
BZX 55/C 27	27		25.1.28.9	<80					20			
BZX 55/C 30	30		28.32						22			
BZX 55/C 33	33		31..35						24			
BZX 55/C 36	36		34.38						27			
BZX 55/C 39	39	2.5	37.41		<500	0.5		<5	30		0.04.0.12	
BZX 55/C 43	43		40.46		<500				33			
BZX 55/C 47	47		44.50		<600				36			
BZX 55/C 51	51		48..54		<700			<1000	39	0.05.0.12		
BZX 55/C 56	56		52.60		<700							43
BZX 55/C 62	62		58.66		<1000							47
BZX 55/C 68	68		64..72									51
BZX 55/C 75	75		70..79									56
BZX 55/C 82	82		77.87		<1500							0.25
BZX 55/C 91	91	85.96		<2000	0.1	68						
BZX 55/C 100	100	94.106		<5000		75						
BZX 55/C 110	110	104.116		<5000		82						
BZX 55/C 120	120	114.127		<5500		91						
BZX 55/C 130	130	124.141		<6000		100						
BZX 55/C 150	150	138.156		<6500		110						
BZX 55/C 160	160	153.171		<7000		120						
BZX 55/C 180	180	168.191		<8500		130						
BZX 55/C 200	200	188.212		<10000				150				

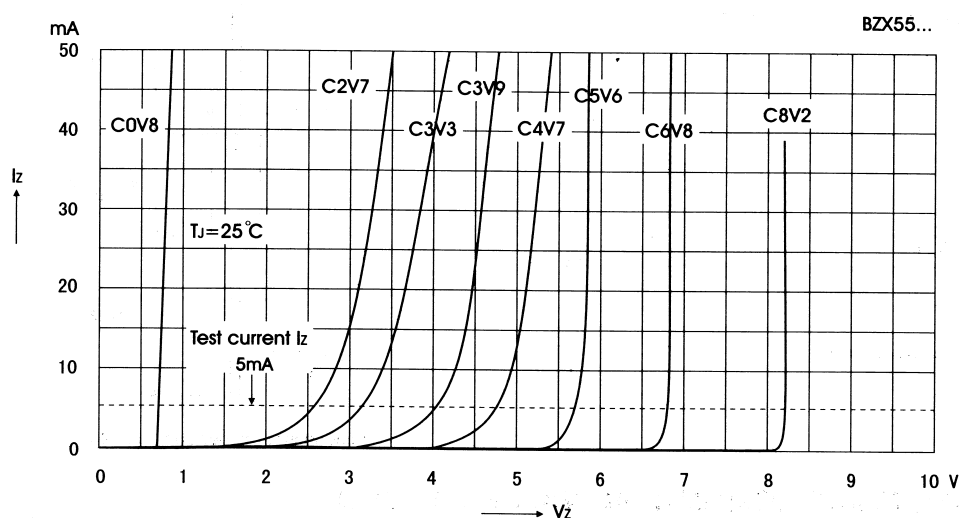
1) Tested with pulses $t_p=20\text{ms}$

2) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case

3) The BZX55-C0V8 is silicon diode with operation in forward direction. Hence, the index of all parameters should be 'F' instead of 'Z'. Connect the cathode lead to the negative pole.

BZX55... SILICON PLANAR ZENER DIODES

BREAKDOWN CHARACTERISTICS AT $T_J = \text{CONSTANT}$ (PULSED)



BREAKDOWN CHARACTERISTICS AT $T_J = \text{CONSTANT}$ (PULSED)

